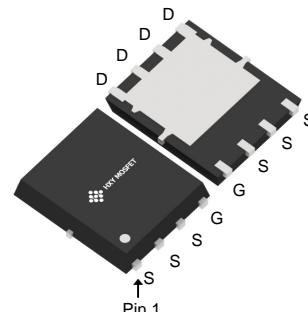




## Description

The HXY30P06NF uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



DFN5X6-8L

$V_{DS} = -600V$   $I_D = -30A$

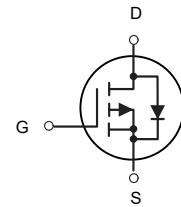
$R_{DS(ON)} < 30m\Omega$   $V_{GS} = -10V$

## Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

## Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HXY30P06NF	DFN5X6-8L	HXY MOSFET	5000

## Absolute Maximum Ratings ( $T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-50	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	-30	A
$I_D @ T_c = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	-25.5	A
$I_{DM}$	Pulsed Drain Current	-144	A
EAS	Single Pulse Avalanche Energy	196	mJ
$P_D @ T_c = 25^\circ C$	Total Power Dissipation	79	W
$T_{STG}$	Storage Temperature Range	-150 to 175	°C
$T_J$	Operating Junction Temperature Range	-150 to 175	°C
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.9	°C/W



**Electrical Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$ , $I_{\text{D}}=-250\mu\text{A}$	-60			V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}}=-60\text{V}$ , $V_{\text{GS}}=0\text{V}$			-1	$\mu\text{A}$
$I_{\text{GSS}}$	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$ , $V_{\text{DS}}=0\text{V}$			$\pm 100$	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$ , $I_{\text{D}}=-250\mu\text{A}$	-1	-1.8	-2.5	V
$g_{\text{FS}}$	Forward Transconductance	$V_{\text{DS}}=-5\text{V}$ , $I_{\text{D}}=-15\text{A}$		35		S
$R_{\text{DS(ON)}}$	Drain-Source On-State Resistance	$V_{\text{GS}}=-10\text{V}$ , $I_{\text{D}}=-15\text{A}$		24	30	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}$ , $I_{\text{D}}=-10\text{A}$		30	40	$\text{m}\Omega$
<b>Dynamic Characteristics</b>						
$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}}=-25\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1.0\text{MHz}$		4026		pF
$C_{\text{oss}}$	Output Capacitance			134		pF
$C_{\text{rss}}$	Reverse Transfer Capacitance			98		pF
<b>Switching Parameters</b>						
$t_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{GS}}=-10\text{V}$ , $V_{\text{DS}}=-30\text{V}$ , $R_{\text{L}}=1.5\Omega$ , $R_{\text{GEN}}=3\Omega$		12.2		nS
$t_r$	Turn-on Rise Time			10		nS
$t_{\text{d(off)}}$	Turn-Off Delay Time			64		nS
$t_f$	Turn-Off Fall Time			14		nS
$Q_g$	Total Gate Charge	$V_{\text{GS}}=-10\text{V}$ , $V_{\text{DS}}=-30\text{V}$ , $I_{\text{D}}=-20\text{A}$		68		nC
$Q_{\text{gs}}$	Gate-Source Charge			10.5		nC
$Q_{\text{gd}}$	Gate-Drain Charge			13		nC
<b>Source-Drain Diode Characteristics</b>						
$I_{\text{SD}}$	Source-Drain Current (Body Diode)				30	A
$V_{\text{SD}}$	Forward on Voltage (Note 3)	$V_{\text{GS}}=0\text{V}$ , $I_{\text{S}}=-15\text{A}$			-1.2	V
$t_{\text{rr}}$	Reverse Recovery Time	$I_{\text{F}}=-20\text{A}$ , $\text{d}I/\text{d}t=100\text{A}/\mu\text{s}$		26		ns
$Q_{\text{rr}}$	Reverse Recovery Charge	$I_{\text{F}}=-20\text{A}$ , $\text{d}I/\text{d}t=100\text{A}/\mu\text{s}$		29		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

Notes 2.E<sub>AS</sub> condition:  $T_J=25^\circ\text{C}$ ,  $V_{\text{DD}}=40\text{V}$ ,  $V_{\text{G}}=-10\text{V}$ ,  $R_{\text{G}}=25\Omega$ ,  $L=0.5\text{mH}$ .

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



## Typical Performance Characteristics

Figure 1. Output Characteristics

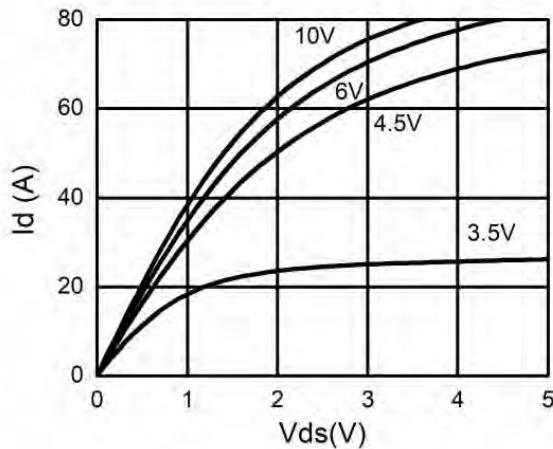


Figure 2. Transfer Characteristics

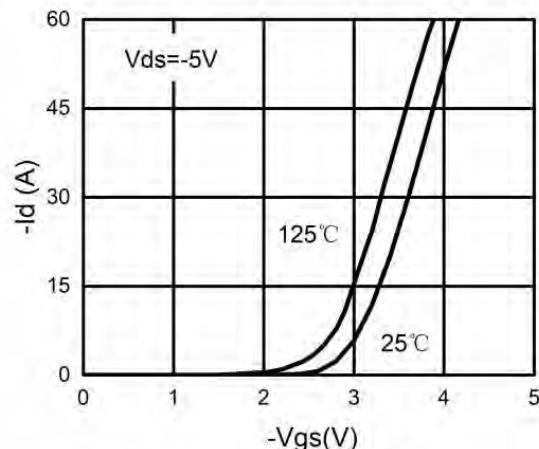


Figure 3. Power Dissipation

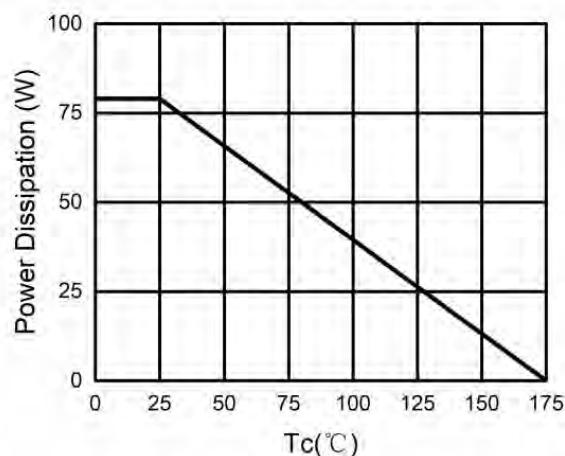


Figure 4. Drain Current

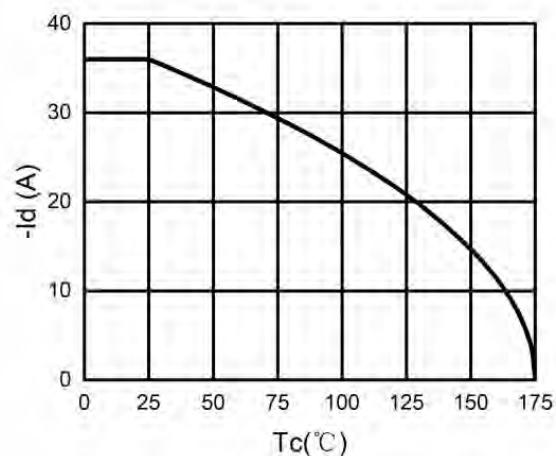


Figure 5.  $BV_{DSS}$  vs Junction Temperature

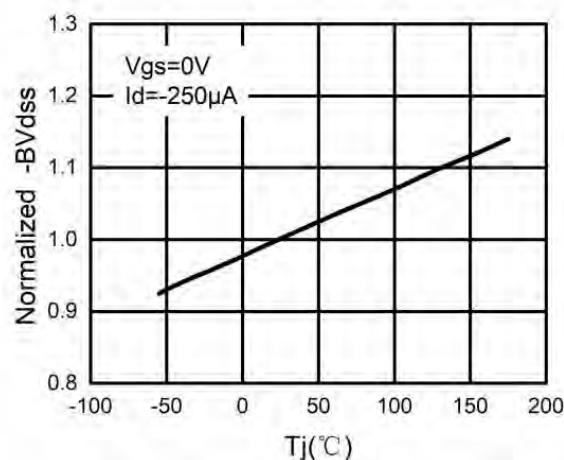


Figure 6.  $R_{DS(ON)}$  vs Junction Temperature

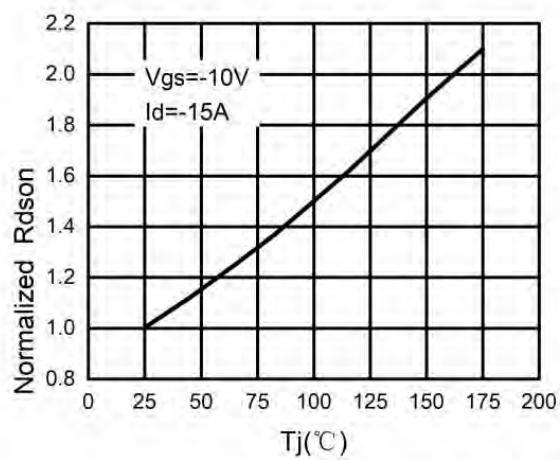




Figure 7. Gate Charge Waveforms

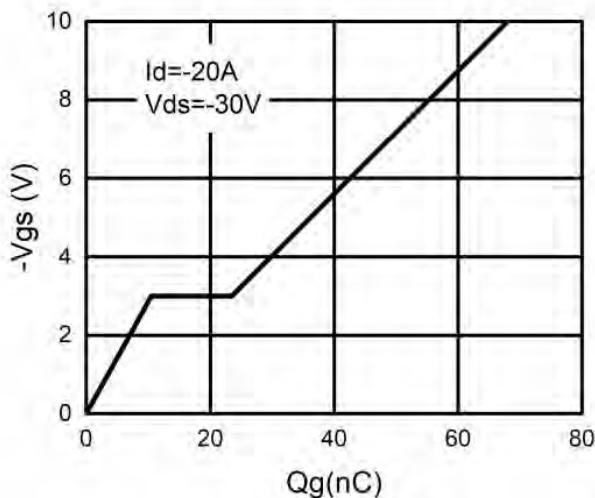


Figure 8. Capacitance

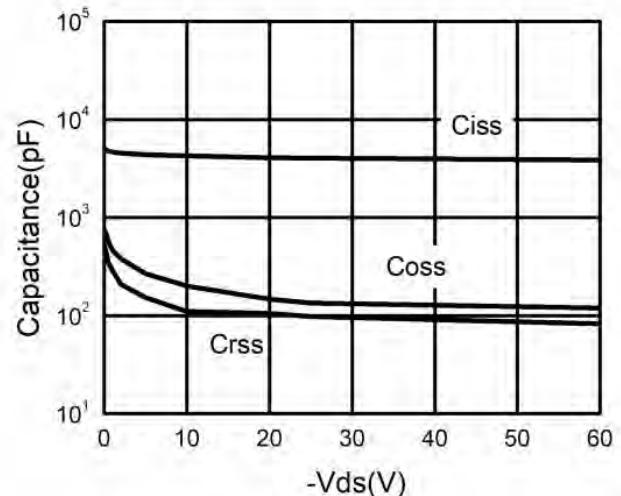


Figure 9. Body-Diode Characteristics

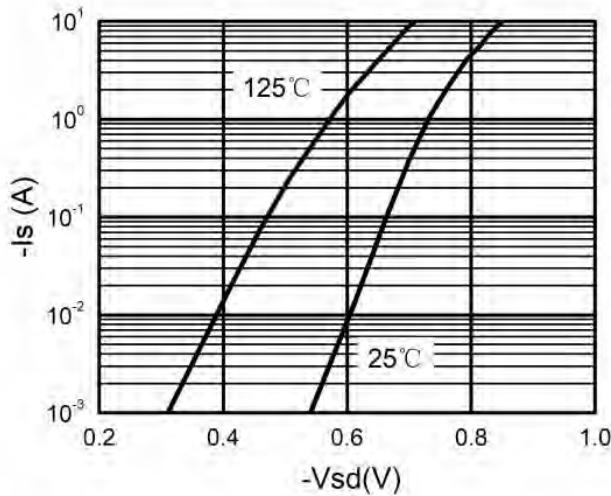
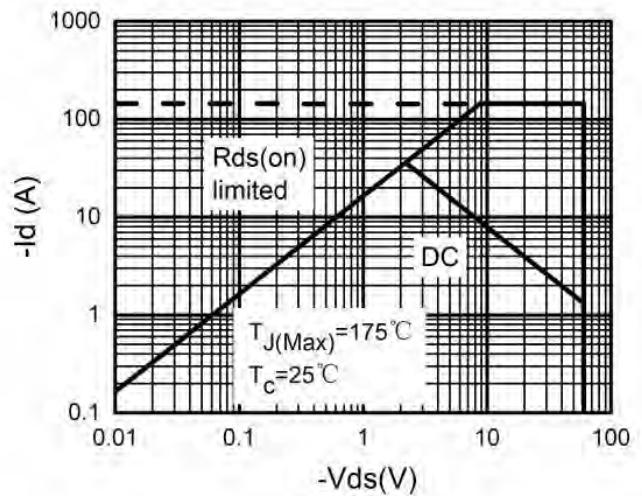
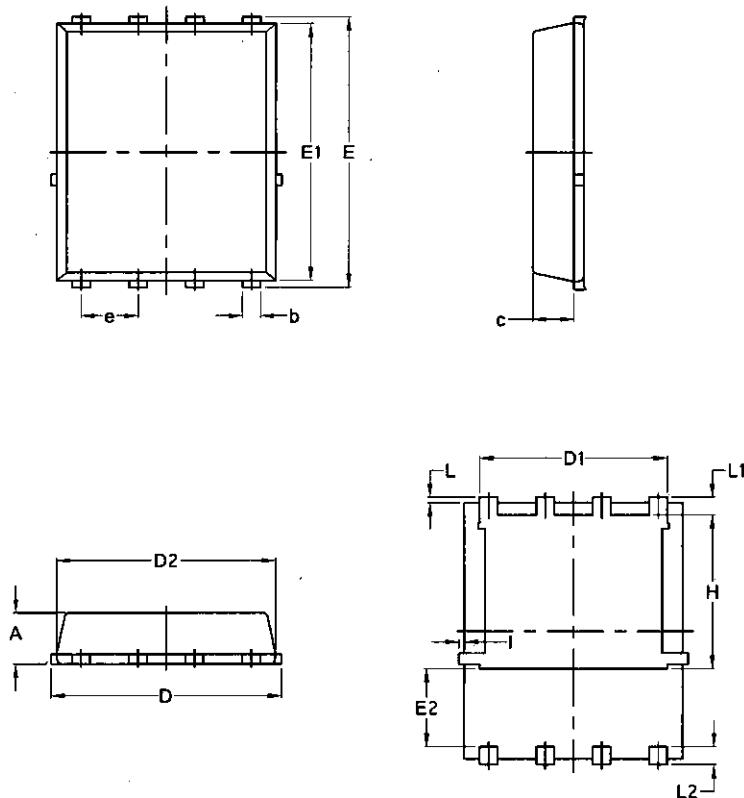


Figure 10. Maximum Safe Operating Area





### DFN5X6-8L Package Information



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070



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